



## FEATURES

- Class AB linear LDMOS design
- Instantaneous ultra-wide bandwidth
- Suitable for all single channel modulation standards
- Small form factor and light weight
- Built-in protection circuits
- High reliability and ruggedness

## ELECTRICAL SPECIFICATIONS: 50Ω, 25 °C

Parameter	Specification	Notes
Operating Frequency Range	0.25 - 1000 MHz	
Output Power @ Psat	10 Watt Min	CW
Power Gain	40 dB Min	
Power Gain Flatness	4 dB p-p Max	Constant input power
Input Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	<-30 dBc Typ	30dBm/Tone, Δ = 1MHz
Harmonics @ Rated Pout	2 <sup>nd</sup>	-14 dBc Typ
	3 <sup>rd</sup>	-25 dBc Typ
Spurious	-60dBc Max	Non-harmonics
Noise Figure	<10 dB Typ	
Operating Voltage	28 - 30 VDC	
Current Consumption	2 Amp Max	At rated Pout
Max Input Power	+8 dBm	<10 Sec without damage
Load VSWR Protection	∞ : 1	<1 minute at rated Pout

## ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

## MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	125 x 63 x 27 mm	Excluding connectors
Weight	350 gr.	
RF Connectors In/Out	SMA female	
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

## D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	FWD	N/A
2	VVA	N/C
3	CURRENT SENSOR	I <sub>b</sub> @50mV/100mA Typ
4	TEMP SENSOR	V <sub>T</sub> @10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
6, 7	VDD	28VDC
8, 9	GND	Ground

# AMP1067 SOLID STATE HIGH POWER AMPLIFIER

## OUTLINE DRAWING

